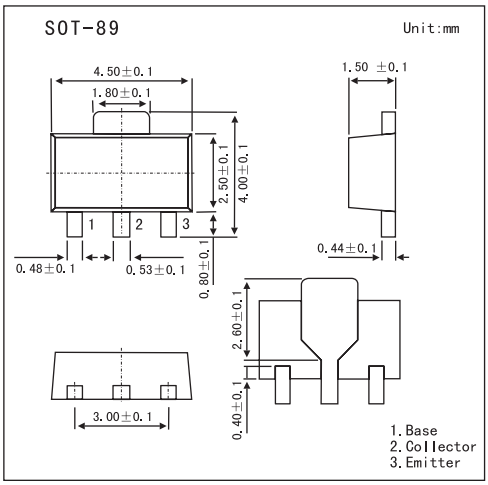
Silicon PNP Epitaxial

2SB1026



■ Features

- Low frequency power amplifier

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V_{CEO}	-100	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Collector peak current	$i_{C(peak)}$*1	-2	A
Collector power dissipation	P_C*2	1	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to 150	℃

*1 PW ⩽ 10 ms, Duty cycle ⩽ 20%

*2 Value on the alumina ceramic board (12.5X 20X 0.7 mm)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = -10 μA, I_E = 0	-120			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1 mA, R_{BE} = ∞	-100			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = -10 μA, I_C = 0	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -100 V, I_E = 0			-10	μA
DC current transfer ratio	h_{FE}	V_{CE} = -5 V, I_C = -150mA,	60		200	
		V_{CE} = -5 V, I_C = -500mA	30			
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = -0.5 A, I_B = -50 mA,			-1.0	V
Base to emitter voltage	V_{BE}	V_{CE} = -5 V, I_C = -150mA,			-0.9	V
Gain bandwidth product	fT	V_{CE} = -5 V, I_C = -150 mA		140		MHz
Collector output capacitance	Cob	V_{CB} = -10 V, I_E = 0,f = 1 MHz		20		pF

■ h_{FE} Classification

Marking	DL	DM
hFE	60 to 120	100 to 200